

UNISONIC TECHNOLOGIES CO., LTD

S8050

NPN SILICON TRANSISTOR

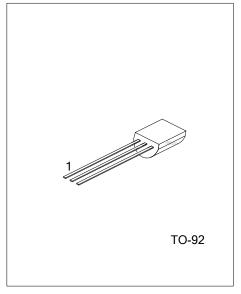
LOW VOLTAGE HIGH **CURRENT SMALL SIGNAL** NPN TRANSISTOR

DESCRIPTION

The UTC \$8050 is a low voltage high current small signal NPN transistor, designed for Class B push-pull audio amplifier and general purpose applications.

FEATURES

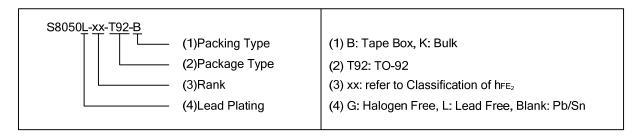
- * Collector current up to 700mA
- * Collector-Emitter voltage up to 20 V
- * Complementary to S8550



Lead-free: S8050L Halogen-free: S8050G

ORDERING INFORMATION

Order Number			Doolsogo	Pin Assignment			Daakina	
Normal	Lead Free Plating	Halogen Free	Package	1	2	3	Packing	
S8050-xx-T92-B	S8050L-xx-T92-B	S8050G-xx-T92-B	TO-92	Е	В	С	Tape Box	
S8050-xx-T92-K	S8050L-xx-T92-K	S8050G-xx-T92-K	TO-92	Е	В	С	Bulk	



www.unisonic.com.tw 1 of 4 QW-R201-013.B

■ ABSOLUTE MAXIMUM RATING (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	Ic	700	mA
Collector Dissipation(Ta=25°C)	Pc	1	W
Junction Temperature	TJ	150	°C
Storage Temperature	T_{STG}	-65 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

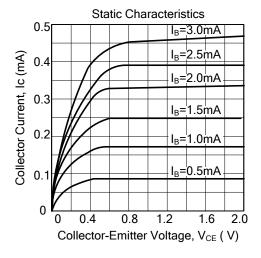
■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

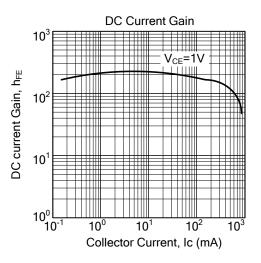
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	Ic=100μA, I _E =0	30			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	Ic=1mA, I _B =0	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =100μA, Ic=0	5			V
Collector Cut-Off Current	I _{CBO}	$V_{CB}=30V$, $I_{E}=0$			1	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} =5V, Ic=0			100	nA
	h _{FE1}	V _{CE} =1V, Ic=1mA	100			
DC Current Gain	h _{FE2}	V _{CE} =1V, Ic=150 mA	120	110	400	
	h _{FE3}	V _{CE} =1V, Ic=500mA	40			
Collector-Emitter Saturation Voltage	V _{CE(SAT})	Ic=500mA, I _B =50mA			0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT})	Ic=500mA, I _B =50mA			1.2	V
Base-Emitter Saturation Voltage	V_{BE}	V _{CE} =1V, Ic=10mA			1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} =10V, Ic=50mA	100			MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		9.0		pF

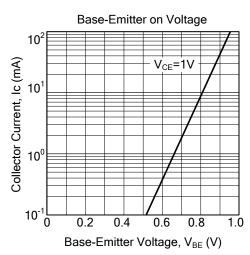
■ CLASSIFICATION OF h_{FE2}

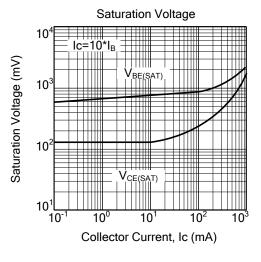
RANK	С	D	E
RANGE	120-200	160-300	280-400

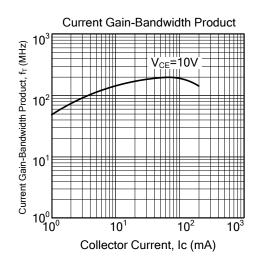
■ TYPICAL CHARACTERISTICS

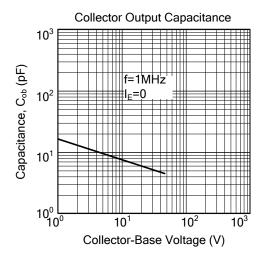












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